N-channel 60 V 2.2 mΩ standard level MOSFET in TO-220 **Product data sheet** 

### 1. General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Robust construction for demanding applications
- Standard level gate

### 3. Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	-	120	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12	[2]	-	1.8	2.2	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; Fig. 12; Fig. 13		-	3	3.5	mΩ
Dynamic char	acteristics						
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V;		-	32	45	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 14; Fig. 15		-	137	192	nC
Avalanche ruç	gedness		'			,	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 120 A; $V_{sup} \le 60$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Unclamped		-	-	913	mJ

- Continuous current limited by package
- Measured 3 mm from package.



# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G—(III)
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package	ackage						
	Name	Description	Version					
PSMN2R0-60PS		plastic, single-ended package (heatsink mounted, 1 mounting hole); 3 leads; 2.54 mm pitch; 15.6 mm x 10 mm x 4.4 mm body	SOT78					

# 7. Marking

**Table 4. Marking codes** 

Type number	Marking code
PSMN2R0-60PS	PSMN2R0 60PS

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	60	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	338	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	120	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	1135	A
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C

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Symbol	Parameter	Conditions		Min	Max	Unit			
Source-drain	Source-drain diode								
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	Α			
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	1135	Α			
Avalanche ru	Avalanche ruggedness								
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 120 A; $V_{sup} \le 60$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Unclamped		-	913	mJ			

#### [1] Continuous current limited by package

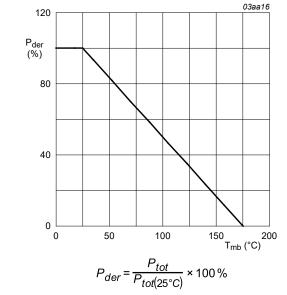
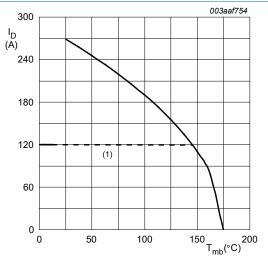
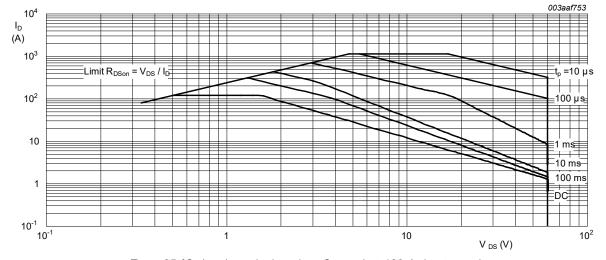


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$ ; (1) Capped at 120 A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature.



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse; Capped at 120 A due to package

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



### 10. Characteristics

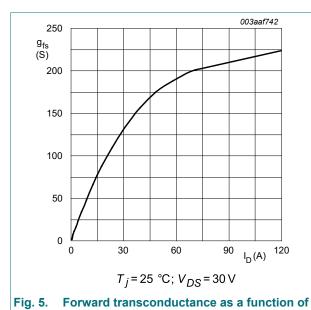
#### **Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	ecteristics				'		_
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C		54	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10		1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 10; Fig. 11$		2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$		-	-	4.6	V
DSS drain leakage curren	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	0.03	10	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C		-	-	1000	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	-	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12	[1]	-	1.8	2.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13		-	4.3	5.1	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13		-	3	3.5	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>G</sub>	gate resistance	f = 1 MHz	0.45	0.9	1.8	Ω
Dynamic ch	aracteristics					
$Q_{G(tot)}$	total gate charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	137	192	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; \frac{\text{Fig. 14}}{\text{Fig. 15}};$	-	129	181	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V;	-	48	68	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 14; Fig. 15	-	29	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	19	-	nC
Q <sub>GD</sub>	gate-drain charge		-	32	45	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 30 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	5.7	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	9997	13500	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	1210	1640	pF
C <sub>rss</sub>	reverse transfer capacitance		-	594	835	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 0.4 \Omega; V_{GS} = 10 \text{ V};$	-	42	63	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	56	84	ns
t <sub>d(off)</sub>	turn-off delay time		-	115	173	ns
t <sub>f</sub>	fall time	1	-	49	74	ns
Source-drai	in diode		· · · · · · · · · · · · · · · · · · ·			
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	57	75	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 30 V	-	80	104	nC
	1	1	1 1	1	1	

#### [1] Measured 3 mm from package.



drain current; typical values

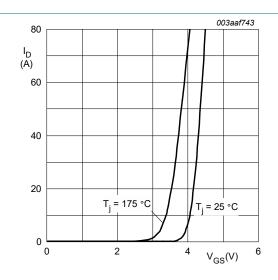


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

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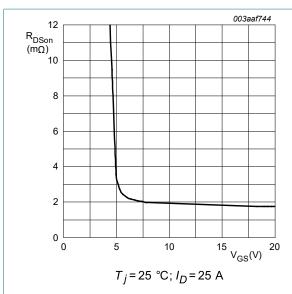


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

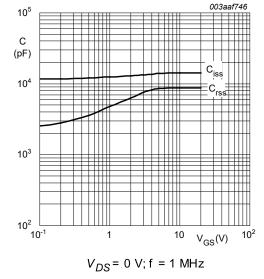


Fig. 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

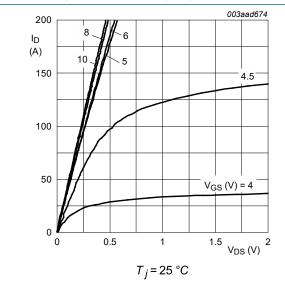


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

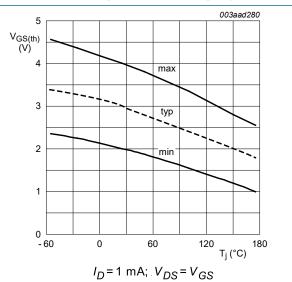


Fig. 10. Gate-source threshold voltage as a function of junction temperature

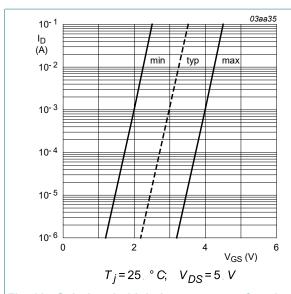


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

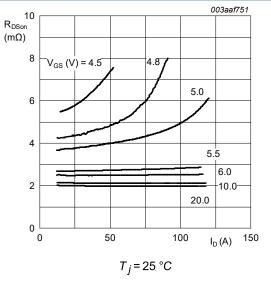
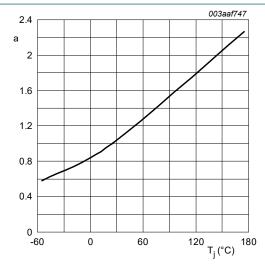


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25 \text{ °C}; I_D = 25 \text{ A}$ 

Fig. 13. Drain-source on-state resistance as a function of gate-source voltage; typical values

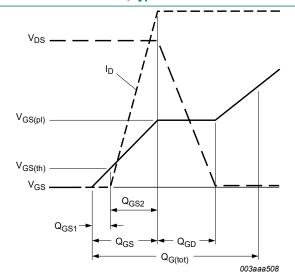


Fig. 14. Gate charge waveform definitions

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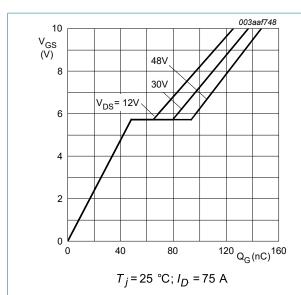


Fig. 15. Gate-source voltage as a function of gate charge; typical values

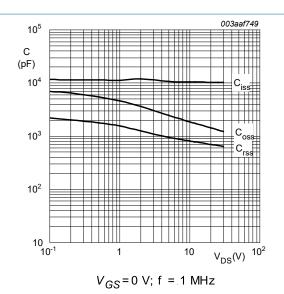


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

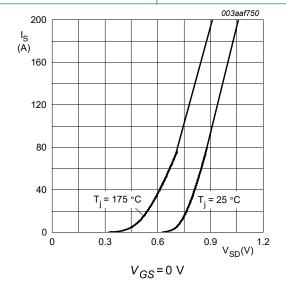
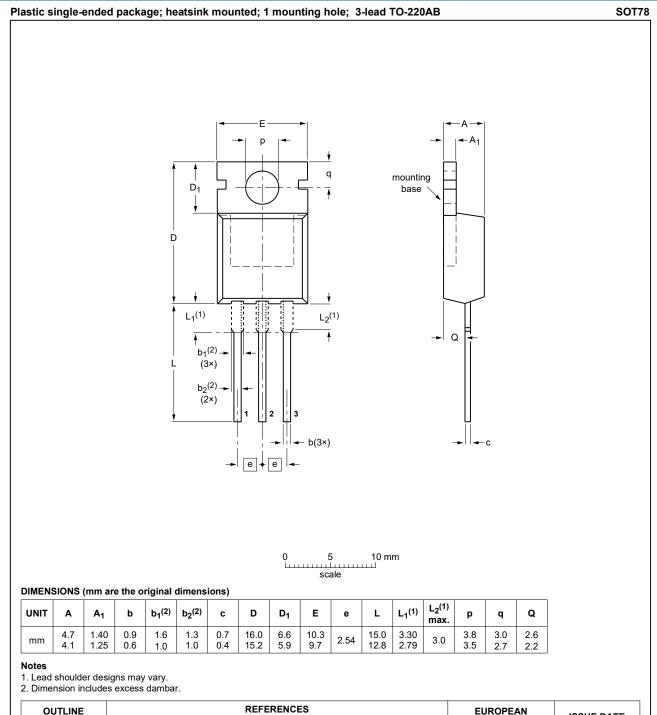


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 11. Package outline



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

Fig. 18. Package outline TO-220AB (SOT78)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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